IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of:)
JUSTIN K. BRASK MARK L. DOCZY SCOTT A. HARELAND JOHN P. BARNAK)))
MATTHEW V. METZ JACK KAVALIEROS ROBERT S. CHAU)))
Serial No.: unknown) Art Unit: unknown)) Examiner: unknown
Filed: unknown) Attorney Docket: P17280
For: A METHOD FOR MAKING A SEMICONDUCTOR DEVICE HAVING A HIGH-K GATE DIELECTRIC))))

Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

INFORMATION DISCLOSURE STATEMENT

Sir:

This Information Disclosure Statement is being submitted under 37 C.F.R. §1.97(b). Enclosed is a copy of Information Disclosure Citation Form PTO-1449 together with copies of the references cited on that form. It is respectfully requested that the cited references be considered and that the enclosed copy of Information Disclosure Citation Form PTO-1449 be initialed by the Examiner to indicate such consideration and a copy thereof returned to applicant(s).

Pursuant to 37 C.F.R. § 1.97, the submission of this Information Disclosure

Statement is not to be construed as a representation that a search has been made

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and is not to be construed as an admission that the information cited in this statement constitutes prior art or is otherwise material to patentability.

Respectfully submitted,

Dated Luget 26, 2003

Mark V. Seeley Reg. No. 32,299

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